Thin film Process: DepositionMetal oxide films by sputtering technique.

Equipment:RF/DC magnetron sputtering system-3(In-house fabricated)

Photograph :

Basic Principle: In this process a gaseous plasma of typically inert gas ions such as Argon (Ar^+) is created and the positive ions are accelerated by an electrical field to the target material which acts as the negatively charged electrode. The atoms from the target materials are ejected by bombardment of energetic ions and deposited on the desired substrate to form a film of the target materials.

Capabilities: Both RF / DC sputtering, Fully manual operation, substrate temperature upto 700 °C.

Sample Requirement: Maximum Substrate size 3” x 3”